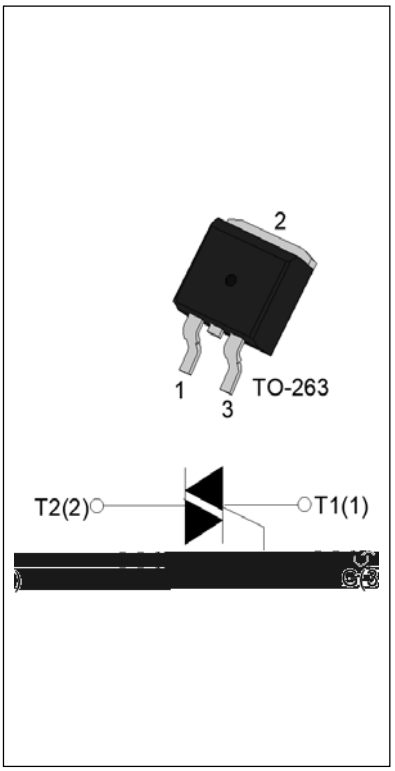
JST12E-800SW 12A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST12E-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST12E-800SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package TO-263 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} /V_{RRM}	800	V
I_{GT} / /	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
RMS on-state current ($T_C \leq$ 103)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)		132	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	72	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT} , f=100Hz , T_j=125)	dI/dt	50	A s
Peak gate current (t_p=20 s , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	25	mA
				30	
I_H	I_T =500mA		MAX.	15	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	400	V s
(dI/dt)c	(dV/dt)c=1 j=125		MIN.	3	A/ms
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	2.5	s
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =17A t_p=380 s	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	35	
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	0.5	

ORDERING INFORMATION

J ST 12 E -800 E29 69]/BBo5.0

FIG.1: Maximum power dissipation versus RMS on-state current

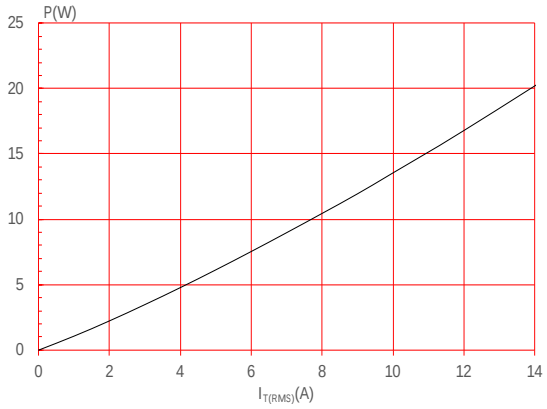


FIG.2: RMS on-state current versus case temperature

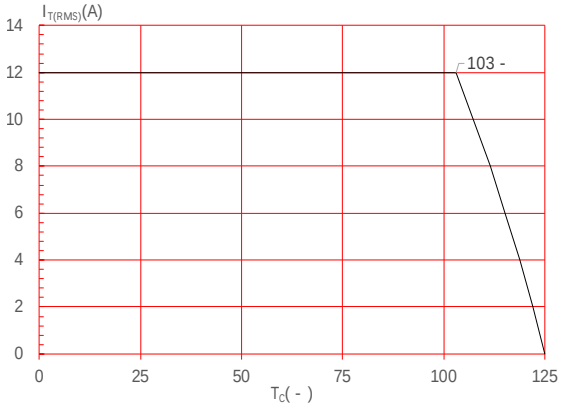


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper

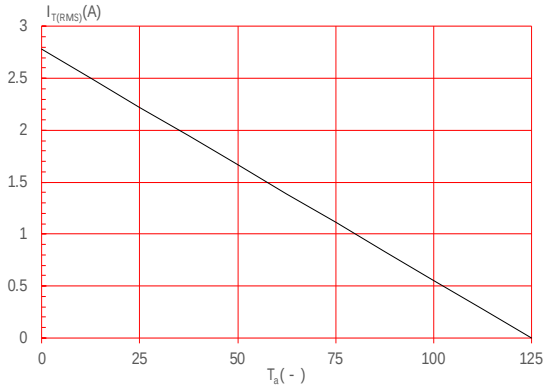


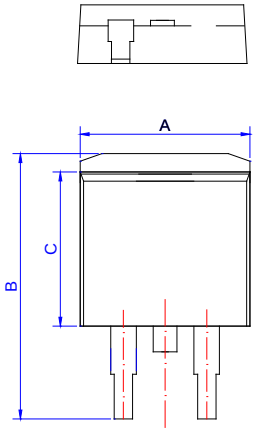
FIG.4: Surge peak on-state current versus number of cycles

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
JST12E-800SW	800	10	TO-263	50	Tube

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033